

ABSTRACT OF THE DISCLOSURE

A stabilized capacitor using non-oxide electrodes and high dielectric constant oxide dielectric materials and methods of making such capacitors and their incorporation into DRAM cells is provided. A preferred method includes providing a non-oxide electrode, oxidizing an upper surface of the non-oxide electrode, depositing a high dielectric constant oxide dielectric material on the oxidized surface of the non-oxide electrode, and depositing an upper layer electrode on the high dielectric constant oxide dielectric material.

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